## TISP1070H3BJ THRU TISP1120H3BJ

## DUAL FORWARD-CONDUCTING UNIDIRECTIONAL THYRISTOR OVERVOLTAGE PROTECTORS

The TISP1xxxH3BJ series is obsolete and not recommended for new designs.

# TISP1xxxH3BJ Overvoltage Protector Series

**Overvoltage Protection for Negative Rail SLICs** SMB03 Package (Top View) **Dual High Current Protectors in a Space Efficient Package** - 2 x 100 A 10/1000 Current Rating 1 | - SMB03 Package (3-pin Modified SMB/DO-214AA) 2 50 % Space Saving over Two SMBs 3 Ion-Implanted Breakdown Region MDXXCJA - Precise and Stable Voltage - Low Voltage Overshoot under Surge **Device Symbol** V<sub>DRM</sub> V<sub>(BO)</sub> **Device Name** 3 V V R) (R or T) TISP1070H3BJ -58 -70 TISP1080H3BJ -65 -80 TISP1095H3BJ -75 -95 TISP1120H3BJ -95 -120 **Rated for International Surge Wave Shapes I<sub>PPSM</sub>** SD1TAA Wave Shape Standard A 2 (G) 2/10 GR-1089-CORE 500 IEC 61000-4-5 8/20 300 TIA-968-A (FCC Part 68 10/160 200 .....UL Recognized Component 10/700 ITU-T K.20/21/45 150 10/560 TIA-968-A (FCC Part 68) 120 10/1000 GR-1089-CORE 100

#### Description

These dual unidirectional thyristor devices protect SLICs and ISDN power feeds in central office, access and customer premises equipment against overvoltages on the telecom line. Each protector section consists of a voltage-triggered unidirectional thyristor with an anti-parallel diode. In the negative polarity, the thyristor allows signal voltages, without clipping, up to the maximum off-state voltage value,  $V_{DRM}$ , see Figure 1. Voltages exceeding  $V_{DRM}$  are limited and will not exceed the breakover voltage,  $V_{(BO)}$ , level. If sufficient current flows due to the overvoltage, the thyristor switches into a low-voltage on-state condition, which diverts the current from the overvoltage through the thyristor. When the diverted current falls below the holding current,  $I_{\mu}$ , level the thyristor switches off and restores normal system operation. Positive overvoltages are limited by the conduction of the anti-parallel diode.

The TISP1xxxH3BJ is available in four voltages and has a 100 A 10/1000 current rating. These protectors have been designed particularly for use in equipment that must meet the following standards and recommendations: GR-1089-CORE, TIA-968-A (replaces FCC Part 68), ITU-T K.20, K.21 and K.45. Housed in a SMB03 package (3-pin modified SMB/DO-214AA), these parts are space efficient to replace protection designs of 100 A 10/1000 or less which use multiple SMBs or a 6-pin SMT package.

### How to Order

Device	Package	Carrier	Order As	Marking Code	Std. Qty.
TISP1xxxH3BJ	SMB03 (3-pin modified SMB/DO-214AA)	Embossed Tape Reeled	TISP1xxxH3BJR-S	1xxxH3	3000

Insert xxx value corresponding to device name.

\*RoHS Directive 2002/95/EC Jan 27 2003 including Annex JUNE 2003 - REVISED MAY 2011 Specifications are subject to change without notice.

Customers should verify actual device performance in their specific applications.



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#### Absolute Maximum Ratings, T<sub>A</sub> = 25 °C (Unless Otherwise Noted)

Rating	Symbol	Value	Unit
'1070		-58	V
Benetitive neak off-state voltage (Terminals 1-2 and 3-2) (see Note 1)	Vanu	-65	
1095	♥ DRM	-75	v
'1120		-95	
Non-repetitive peak on-state pulse current (see Notes 2 and 3)			
2/10 (Telcordia GR-1089-CORE, 2/10 voltage wave shape)		2x500	
8/20 (IEC 61000-4-5, combination wave generator, 1.2/50 voltage wave shape)		2x300	
10/160 (TIA-968-A (replaces FCC Part 68), 10/160 $\mu s$ voltage wave shape)	I <sub>PPSM</sub>	2x200	A
5/310 (ITU-T K.44, 10/700 $\mu s$ voltage wave shape used in K.20/45/21)		2x150	
5/320 (TIA-968-A (replaces FCC Part 68), 9/720 $\mu s$ voltage wave shape)		2x150	
10/560 (TIA-968-A (replaces FCC Part 68), 10/560 $\mu s$ voltage wave shape)		2x120	
10/1000 (Telcordia GR-1089-CORE, 10/1000 voltage wave shape)		2x100	
Non-repetitive peak on-state current (see Notes 2 and 3)			
50 Hz, 1 cycle	l	2x30	Δ
60 Hz, 1 cycle	TSM	2x35	~
1000 s 50 Hz/60 Hz a.c.		2x1.2	
Initial rate of rise of on-state current, Linear current ramp, Maximum ramp value < 50 A	di <sub>T</sub> /dt	500	A/μs
Junction temperature	TJ	-40 to +150	°C
Storage temperature range	T <sub>stg</sub>	-65 to +150	°C

NOTES: 1. At -40 °C derate linearly to 0.93 × V<sub>DFM</sub> (25 °C) 2. Initially the device must be in thermal equilibrium with T<sub>J</sub> = 25 °C.

3. These non-repetitive rated currents are peak values of either polarity. The rated current values are applied to the terminals 1 and 3 simultaneously (in this case the terminal 2 return current will be the sum of the currents applied to the terminals 1 and 3). The surge may be repeated after the device returns to its initial conditions.

### Electrical Characteristics for the 1 and 2 or the 3 and 2 Terminals, T<sub>A</sub> = 25 °C (Unless Otherwise Noted)

	Parameter	Test Conditions		Min	Тур	Max	Unit
	Repetitive peak off-	$\mathcal{M} = \mathcal{M}$	T <sub>A</sub> = 25 °C			-5	۸
DRM	state current	VD = VDRM	$T_A = 85 \ ^\circ C$			-10	μΑ
			'1070			-70	
V <sub>(BO)</sub>	AC breakover voltage	dv/dt = -250 V/ms, $R_{SOURCE} = 300 \Omega$	'1080			-80	v
			'1095			-95	
			'1120			-120	
I <sub>(BO)</sub>	Breakover current	dv/dt = -250 V/ms, R <sub>SOURCE</sub> = 300 $\Omega$				-800	mA
Ι <sub>Η</sub>	Holding current	$I_T = -5 \text{ A,d i/dt} = +30 \text{ mA/ms}$		-150			mA
du/dt	Critical rate of rise of	Linear voltage romp. Maximum romp volue < 0.95 x V		Б			k)//o
av/at	off-state voltage	Linear voltage ramp, Maximum ramp value < 0.65 x v <sub>DRM</sub>		-0			κν/μ5
ID	Off-state current	V <sub>D</sub> = -50 V	T <sub>A</sub> = 85 °C			-10	μA
V <sub>F</sub>	Forward voltage	$I_{\rm F} = +5 \text{ A,t }_{\rm W} = 500 \ \mu \text{s}$				3	V

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### Electrical Characteristics for the 1 and 2 or the 3 and 2 Terminals, $T_A = 25$ °C (Unless Otherwise Noted)

	Parameter	Test Conditions		Min	Тур	Max	Unit
C <sub>off</sub> Off-state capacit			070		161		
		$f = 1 M H_{7} + 1 V = 1 V rm (V = 2) V$	080		152		
		$v_d = v_d = v_d = v_d$	095		139		
	011	1	120		116		
	Off-state capacitance		070		58		рг
		$f = 1 M H_{7} + 1 V = 1 V rm (V = 50 V)$	080		55		
		$v_{\rm d} = 100000000000000000000000000000000000$	095		50		
		1	120		42		

#### **Thermal Characteristics**

Parameter	Test Conditions Min	Тур	Max	Unit
	EIA/JESD51-3 PCB, T <sub>A</sub> = 25 °C, (see Note 4)		113	
$H_{\theta JA}$ Junction to hee an thermal resistance	265 mm x 210 mm populated line card, 4-layer PCB, $I_T = I_{TSM(1000)}$ , $T_A = 25 °C$	52		-C/W

NOTE 4: EIA/JESD51-2 environment and PCB have standard footprint climensions connected with 5 A rated printed wiring track widths.

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**Typical Characteristics** 



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**Typical Characteristics (Continued)** 



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